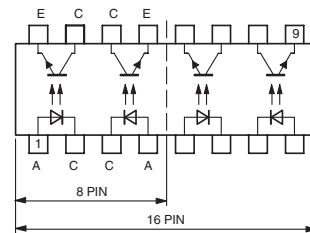
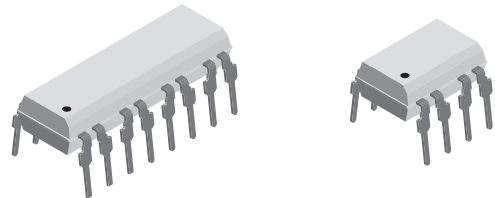


## Optocoupler, Phototransistor Output, Multichannel

### Features

- CNY74-2H includes 2 isolator channels
- CNY74-4H includes 4 isolator channels
- Isolation test voltage  $V_{ISO} = 5000 V_{RMS}$
- Test class 25/100/21 DIN 40 045
- Low coupling capacitance of typical 0.3 pF
- **Current Transfer Ratio (CTR)** of typical 100 %
- Low temperature coefficient of CTR
- Wide ambient temperature range
- Coupling System U
- Lead-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



### Agency Approvals

- UL1577, File No. E76222 System Code U, Double Protection
- CSA22.2 bulletin 5A

17188



### Applications

Galvanically separated circuits, non-interacting switches

### Description

The CNY74-2H and CNY74-4H consist of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in an 8-pin, resp. 16-pin plastic dual in-line package.

The elements are mounted on one leadframe providing a fixed distance between input and output for highest safety requirements.

### Order Information

Part	Remarks
CNY74-2H	CTR 50 - 600 %, DIP-8
CNY74-4H	CTR 50 - 600 %, DIP-16

### Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Stresses in excess of the absolute Maximum Ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute Maximum Rating for extended periods of the time can adversely affect reliability.

### Input

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		$V_R$	6	V
Forward current		$I_F$	60	mA
Forward surge current	$t_p \leq 10\text{ }\mu\text{s}$	$I_{FSM}$	1.5	A
Power dissipation		$P_{diss}$	100	mW
Junction temperature		$T_j$	125	$^{\circ}\text{C}$

### Output

Parameter	Test condition	Symbol	Value	Unit
Collector emitter voltage		$V_{CEO}$	70	V
Emitter collector voltage		$V_{ECO}$	7	V
Collector current		$I_C$	50	mA
Collector peak current	$t_p/T = 0.5, t_p \leq 10\text{ ms}$	$I_{CM}$	100	mA
Power dissipation		$P_{diss}$	150	mW
Junction temperature		$T_j$	125	$^{\circ}\text{C}$

### Coupler

Parameter	Test condition	Symbol	Value	Unit
AC isolation test voltage (RMS)	$t = 1\text{ min}$	$V_{ISO}^{1)}$	5000	$V_{RMS}$
Total power dissipation		$P_{tot}$	250	mW
Ambient temperature range		$T_{amb}$	- 40 to + 100	$^{\circ}\text{C}$
Storage temperature range		$T_{stg}$	- 55 to + 125	$^{\circ}\text{C}$
Soldering temperature	2 mm from case, $t \leq 10\text{ s}$	$T_{sld}$	260	$^{\circ}\text{C}$

<sup>1)</sup> Related to standard climate 23/50 DIN 50014

### Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

### Input

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	$I_F = 50\text{ mA}$	$V_F$		1.25	1.6	V

### Output

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Collector emitter voltage	$I_C = 1\text{ mA}$	$V_{CEO}$	70			V
Emitter collector voltage	$I_E = 100\text{ }\mu\text{A}$	$V_{ECO}$	7			V
Collector dark current	$V_{CE} = 20\text{ V}, I_F = 0, E = 0$	$I_{CEO}$			100	nA

## Coupler

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
DC isolation test voltage	$t = 2 \text{ s}$	$V_{ISO}^{1)}$	5000			V
Isolation resistance	$V_{IO} = 1000 \text{ V}$ , 40 % relative humidity	$R_{IO}^{1)}$		$10^{12}$		$\Omega$
Collector emitter saturation voltage	$I_F = 10 \text{ mA}$ , $I_C = 1 \text{ mA}$	$V_{CEsat}$			0.3	V
Cut-off frequency	$V_{CE} = 5 \text{ V}$ , $I_F = 10 \text{ mA}$ , $R_L = 100 \Omega$	$f_c$		100		kHz
Coupling capacitance	$f = 1 \text{ MHz}$	$C_k$		0.3		pF

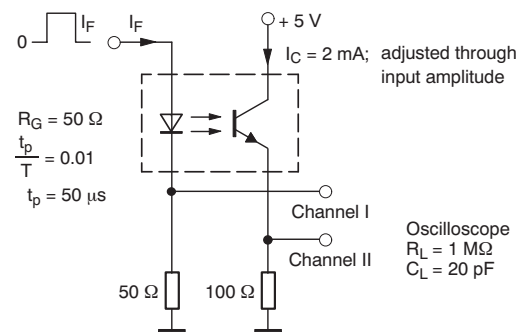
<sup>1)</sup> Related to standard climate 23/50 DIN 50014

## Current Transfer Ratio

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
$I_C/I_F$	$V_{CE} = 5 \text{ V}$ , $I_F = 5 \text{ mA}$	CTR	50	100	600	%
	$V_{CE} = 5 \text{ V}$ , $I_F = 10 \text{ mA}$	CTR	60	120		%

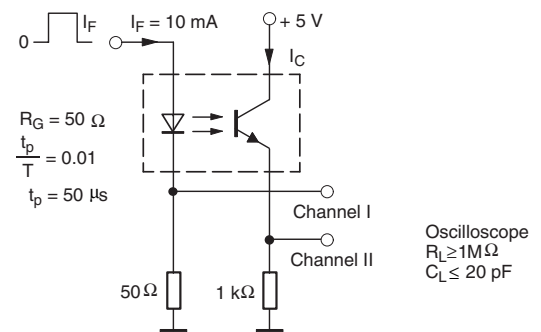
## Switching Characteristics

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Delay time	$V_S = 5 \text{ V}$ , $I_C = 2 \text{ mA}$ , $R_L = 100 \Omega$ (see figure 1)	$t_d$		3.0		$\mu\text{s}$
Rise time	$V_S = 5 \text{ V}$ , $I_C = 2 \text{ mA}$ , $R_L = 100 \Omega$ (see figure 1)	$t_r$		3.0		$\mu\text{s}$
Fall time	$V_S = 5 \text{ V}$ , $I_C = 2 \text{ mA}$ , $R_L = 100 \Omega$ (see figure 1)	$t_f$		4.7		$\mu\text{s}$
Storage time	$V_S = 5 \text{ V}$ , $I_C = 2 \text{ mA}$ , $R_L = 100 \Omega$ (see figure 1)	$t_s$		0.3		$\mu\text{s}$
Turn-on time	$V_S = 5 \text{ V}$ , $I_C = 2 \text{ mA}$ , $R_L = 100 \Omega$ (see figure 1)	$t_{on}$		6.0		$\mu\text{s}$
Turn-off time	$V_S = 5 \text{ V}$ , $I_C = 2 \text{ mA}$ , $R_L = 100 \Omega$ (see figure 1)	$t_{off}$		5.0		$\mu\text{s}$
Turn-on time	$V_S = 5 \text{ V}$ , $I_F = 10 \text{ mA}$ , $R_L = 1 \text{ k}\Omega$ (see figure 2)	$t_{on}$		9.0		$\mu\text{s}$
Turn-off time	$V_S = 5 \text{ V}$ , $I_F = 10 \text{ mA}$ , $R_L = 1 \text{ k}\Omega$ (see figure 2)	$t_{off}$		18.0		$\mu\text{s}$



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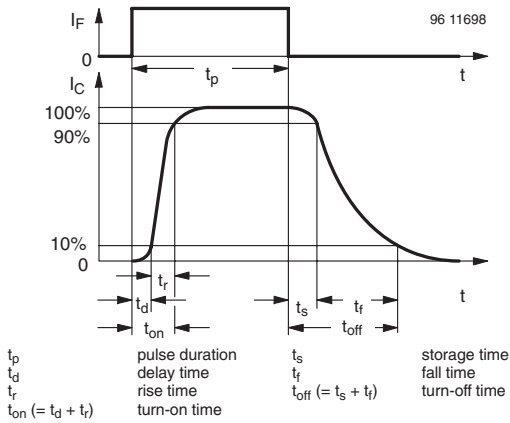
Figure 1. Test circuit, non-saturated operation



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Figure 2. Test circuit, saturated operation

Figure 3. Switching Times



## Typical Characteristics ( $T_{amb} = 25\text{ }^\circ\text{C}$ unless otherwise specified)

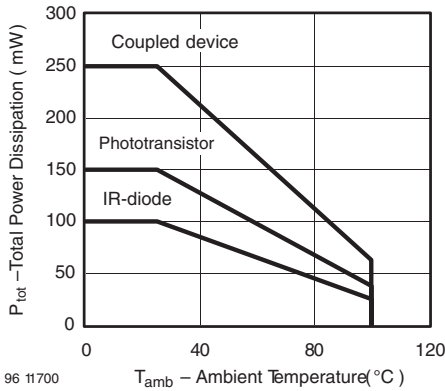


Figure 4. Total Power Dissipation vs. Ambient Temperature

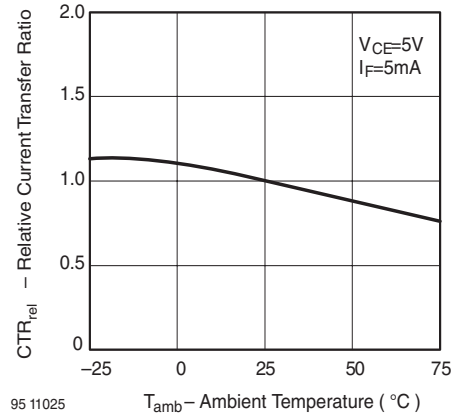


Figure 6. Relative Current Transfer Ratio vs. Ambient Temperature

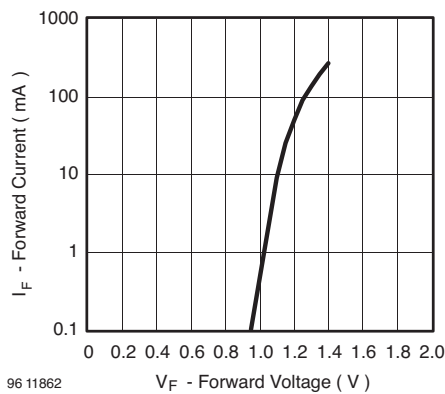


Figure 5. Forward Current vs. Forward Voltage

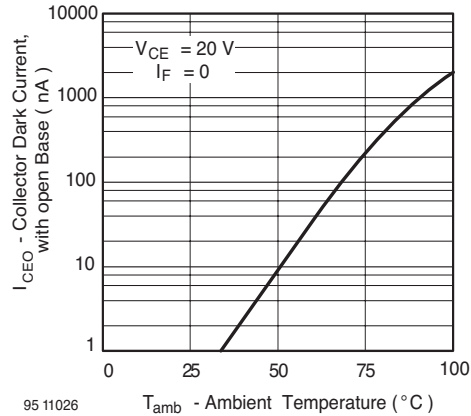
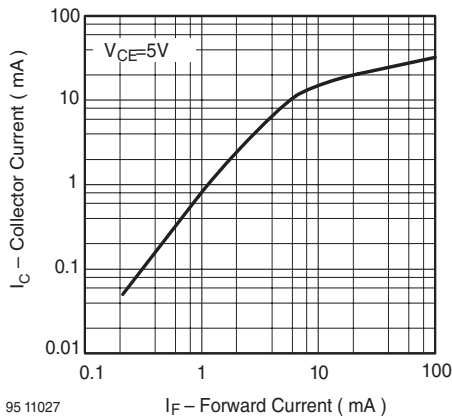
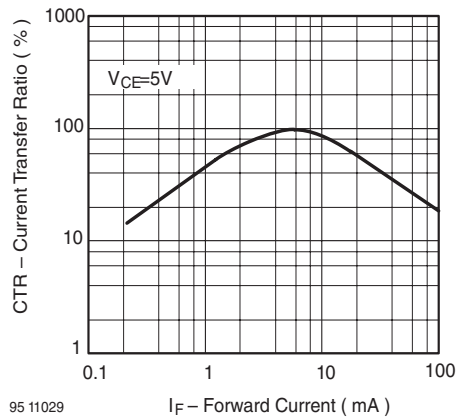


Figure 7. Collector Dark Current vs. Ambient Temperature



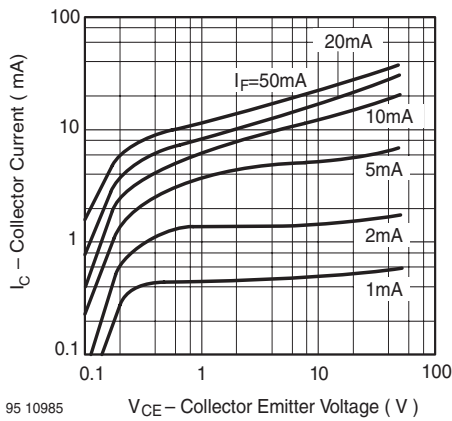
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Figure 8. Collector Current vs. Forward Current



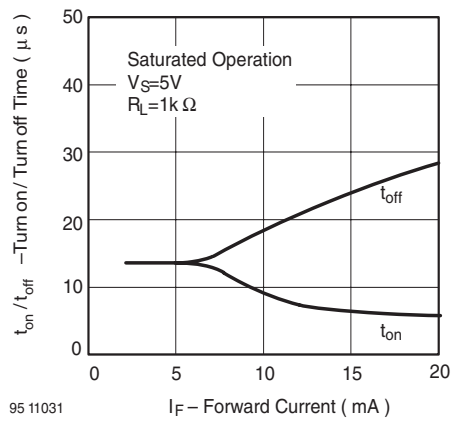
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Figure 11. Current Transfer Ratio vs. Forward Current



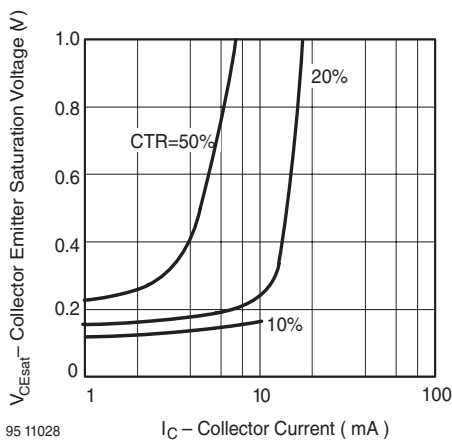
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Figure 9. Collector Current vs. Collector Emitter Voltage



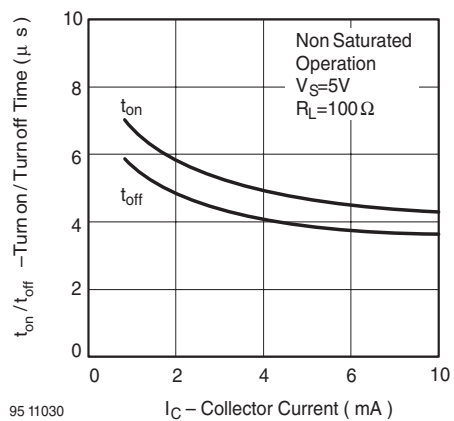
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Figure 12. Turn on / off Time vs. Forward Current



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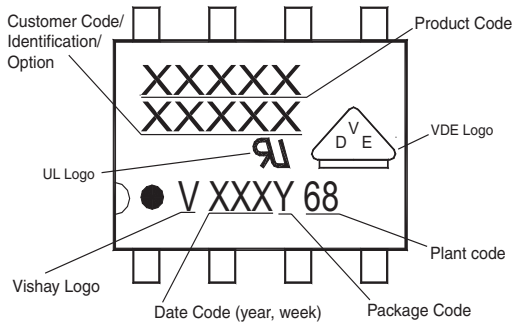
Figure 10. Collector Emitter Saturation Voltage vs. Collector Current



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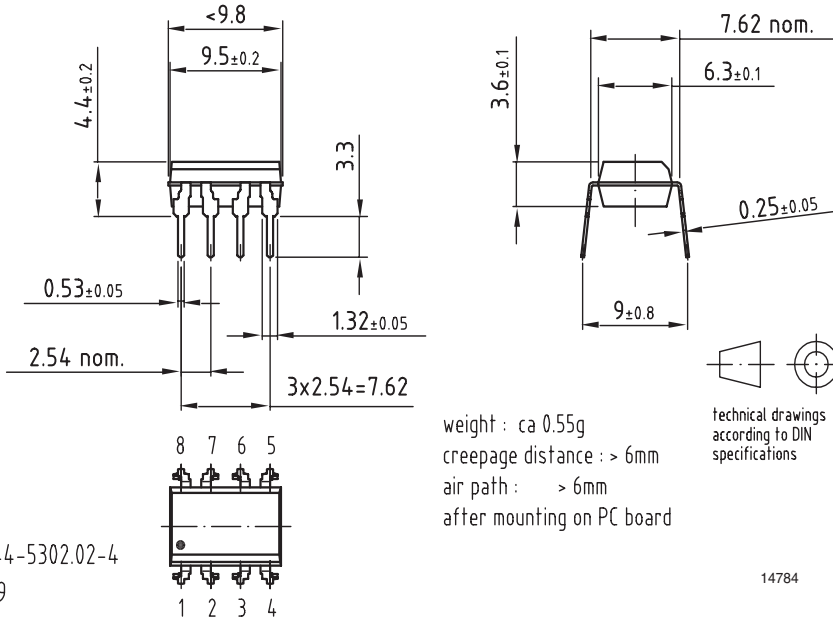
Figure 13. Turn on / off Time vs. Collector Current

Figure 14. Marking example



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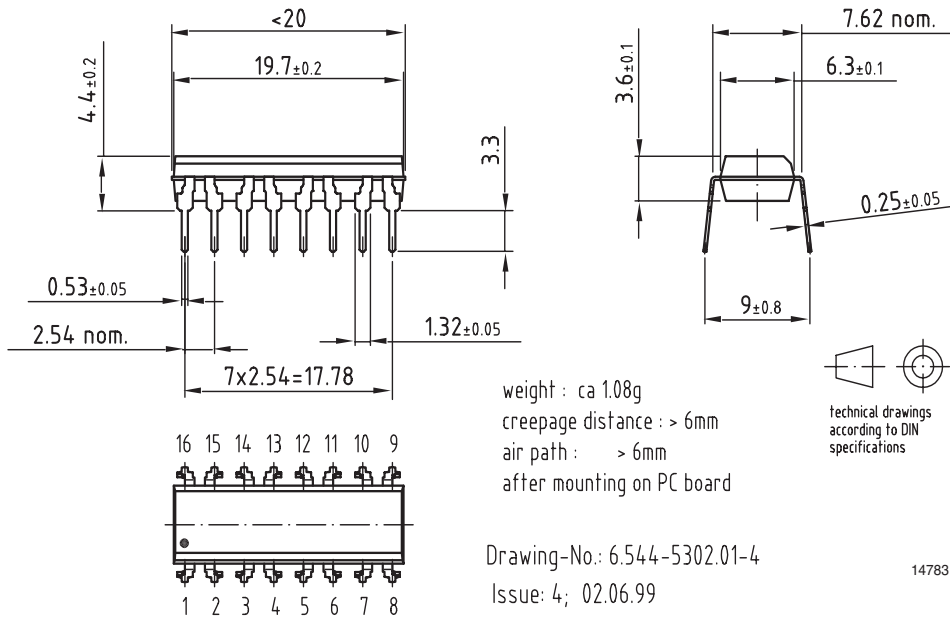
## Package Dimensions in mm



14784

Drawing-No.: 6.544-5302.02-4  
 Issue: 4; 02.06.99

## Package Dimensions in mm



### Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design  
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